

Patent Abstracts of Japan

PUBLICATION NUMBER : 57153431
PUBLICATION DATE : 22-09-82

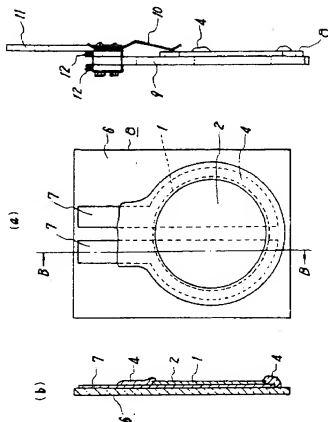
APPLICATION DATE : 17-03-81
APPLICATION NUMBER : 56041378

APPLICANT : MITSUBISHI ELECTRIC CORP;

INVENTOR : TANAKA MAKOTO;

INT.CL. : H01L 21/288 C25D 5/02 C25D 7/12

TITLE : ELECTROPLATING METHOD FOR SEMICONDUCTOR WAFER



ABSTRACT : PURPOSE: To decrease the quantity of wax used by a method wherein two conductive patterns along the shape of the wafer are formed on one surface of a wafer pasted plate consisting of an insulating plate, the surface not plated of the wafer is pasted onto the patterns by using wax, only the plating surface of the wafer is immersed in a plating liquid, and the plating surface is plated.

CONSTITUTION: The conductive patterns 7 mutually separated are formed onto one surface of the insulating plate 6 in left and right symmetrical shapes while being conformed to the shape of the silicon wafer 1, and the wafer 1 is pasted onto the patterns by using wax 4 while directing the plating surface 2 of the wafer 1 to the surface. The wafer pasted plate 8 manufactured in this manner is placed on a plating jig plate 9, the plate 8 is held down by an electrode hold-down plate 10 projected from an electrode plate 12 for a jig shaped at the end section of the jig plate 9, only the plating surface of the surface 2 of the wafer 1 is immersed in the plating liquid, currents are flowed through the patterns 7 while supporting the plate 8 by a handle 11 connected to the conductive patterns 7, and the surface 2 is plated equally. Accordingly, the quantity of the wax 4 used may be decreased, and working hours are also shortened.

COPYRIGHT: (C) JPO